

## **isc** Silicon NPN Power Transistor

## 2SC3170

### DESCRIPTION

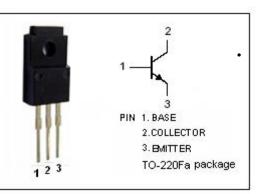
- Collector-Emiiter Sustaining Voltage-: V<sub>CEO(SUS)</sub>= 400V(Min.)
- Low Collector Saturation Voltage
  - : V<sub>CE(sat)</sub>= 1.0V(Max.)@ I<sub>C</sub>= 3A
- High Speed Switching
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

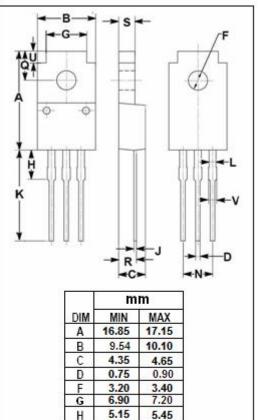
### APPLICATIONS

• Designed for high speed switching applications.

ABSOLUT	E MAXIMUM	RATINGS	(Ta=25 º	C)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>сво</sub>	Collector-Base Voltage	500	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	400	V	
V <sub>EBO</sub>	Emitter-Base Voltage	7	V	
lc	Collector Current-Continuous	7	А	
I <sub>CM</sub>	Collector Current-Peak	15	А	
Pc	Collector Power Dissipation @T <sub>a</sub> =25°C	2	W	
	Collector Power Dissipation @T <sub>C</sub> =25°C	40		
Tj	Junction Temperature	150	°C	
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C	





0.45

13.35

1.10

4.98

4.85

2.55

2.70

1.75

1.30

J

L

Ν

Q

R

SU

v

0.75

13.65

1.30

5.18

5.15

3.25

2.90

2.05

1.50

1

isc website: <u>www.iscsemi.com</u>



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### ELECTRICAL CHARACTERISTICS

#### $T_{\text{C}}\text{=}25^{\circ}\!\!\!^{\circ}\!\!^{\circ}\!\!^{\circ}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> =20mA; I <sub>B</sub> =	400			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 0.6A			1.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 0.6A			1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 500V; I <sub>E</sub> = 0			0.1	mA
Іево	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			0.1	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 5V	15			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 3A; V <sub>CE</sub> = 5V	8			
fT	Current-Gain—Bandwidth Product	Ic= 0.5A; Vce= 10V		8		MHz

Switching Times; Resistive Load

t <sub>on</sub>	Turn-on Time	I <sub>C</sub> = 3A; I <sub>B1</sub> = -I <sub>B2</sub> = 0.6A; V <sub>CC</sub> = 100V		1.0	μs
ts	Storage Time			3.0	μs
t <sub>f</sub>	Fall Time			1.0	μs

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